

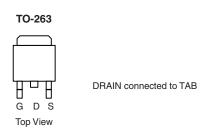
N-Channel 60-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY			
V _{(BR)DSS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)	
60	0.0093 at V _{GS} = 10 V	90	
	0.0135 at V _{GS} = 4.5 V	62	

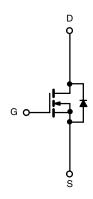
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature





Ordering Information: SUM75N06-09L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unless other	erwise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _{.1} = 175 °C)	T _C = 25 °C		90	۸	
Continuous Diain Guiteri (1) = 173 G)	T _C = 100 °C	- ID	53		
Pulsed Drain Current		I _{DM}	160	A	
Avalanche Current		I _{AR}	50		
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	125	mJ	
Power Dissipation	T _C = 25 °C	В	125 ^b	14/	
	T _A = 25 °C ^c	P _D	3.75 ^c	W	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	(PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case		R _{thJC}	1.2	C/VV

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

SUM75N06-09L

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u>'</u>		l .		<u> </u>	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			- V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μΑ
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			150	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	75			Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V, I _D = 30 A		0.0075	0.0093	
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.0163	Ω
	_	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 175 ^{\circ}\text{C}$			0.024	
	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$		0.0105	0.0135	
		$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}, T_J = 125 ^{\circ}\text{C}$			0.0224	
		$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}, T_J = 175 \text{ °C}$			0.030	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	25	75		S
Dynamic ^b	*		•	•	'	
Input Capacitance	C _{iss}			2400		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		430		
Reversen Transfer Capacitance	C _{rss}			210		
Total Gate Charge ^c	Q_g			47	75	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 90 \text{ A}$		12		
Gate-Drain Charge ^c	Q_{gd}			13		
Turn-On Delay Time ^c	t _{d(on)}			7	12	ns ns
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.4 Ω		30	50	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 90 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		25	40	
Fall Time ^c	t _f			12	20	
Source-Drain Diode Ratings and Cha	racteristics 7	_C = 25 °C ^b				
Continuous Current	I _S				90	^
Pulsed Current	I _{SM}			160	180	Α
Forward Voltage ^a	V _{SD}	I _F = 90 A, V _{GS} = 0 V			1.4	V
Reverse Recovery Time	t _{rr}			40	80	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 50 A, di/dt = 100 A/μs		2	4	Α
Reverse Recovery Charge	Q _{rr}			0.040	0.16	μС

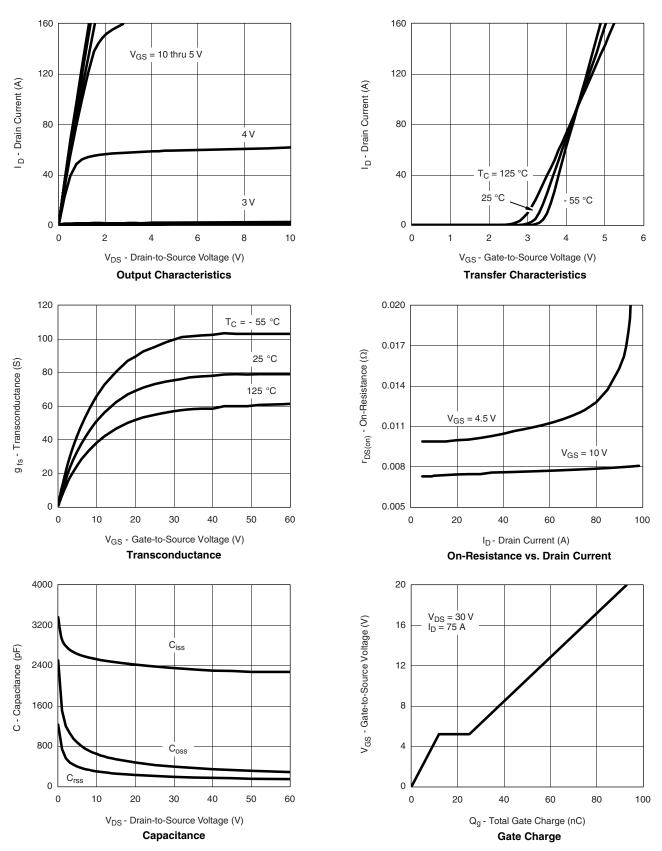
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



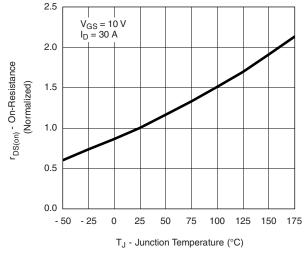
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



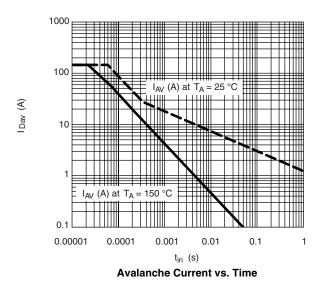
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature



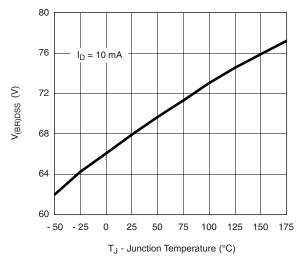
T_J = 150 °C

T_J = 150 °C

T_J = 25 °C

V_{SD} - Source-to-Drain Voltage (V)

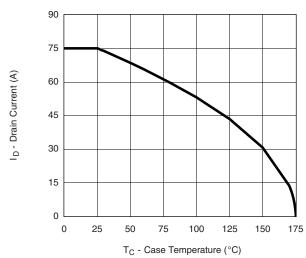
Source-Drain Diode Forward Voltage



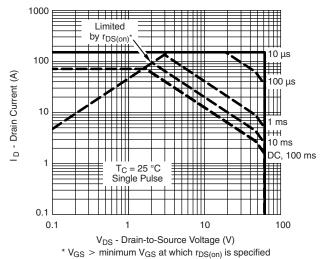
Drain Source Breakdown vs. Junction Temperature



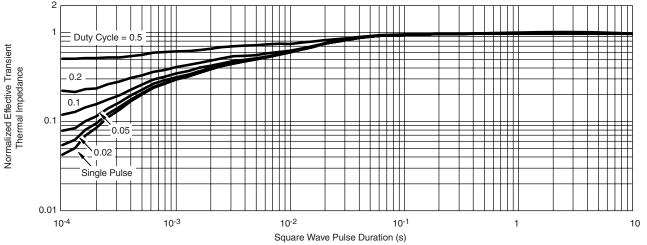
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

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